

# SiPM technology at FBK

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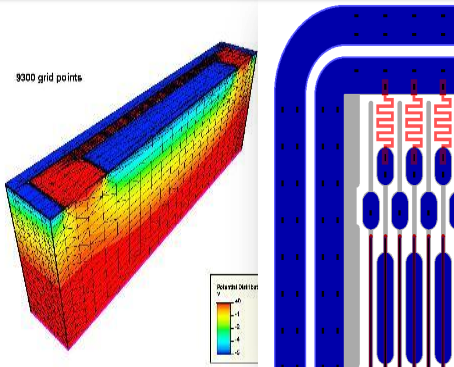
*FBK – Fondazione Bruno Kessler, Trento, Italy*  
*[piemonte@fbk.eu](mailto:piemonte@fbk.eu)*

# Outline

- **FBK fabrication capabilities**
- **FBK SiPM technology**
- **Results achieved during the years**
  - **2006**
  - **2007**
  - **2008**

## Capabilities in silicon technology

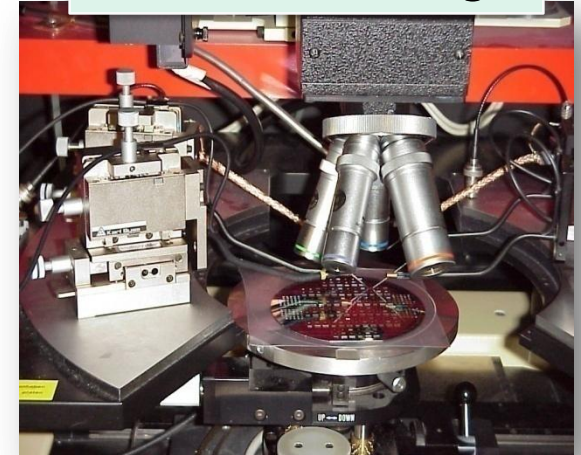
TCAD simulation  
CAD design



Fabrication



Device testing



- 500m<sup>2</sup> lab for silicon device processing.
- no process steps out.
- all autom. equipment.
- 4" wafers.

- 3 automatic probers
- 2 manual probers
- optical bench
- basic lab for functional tests

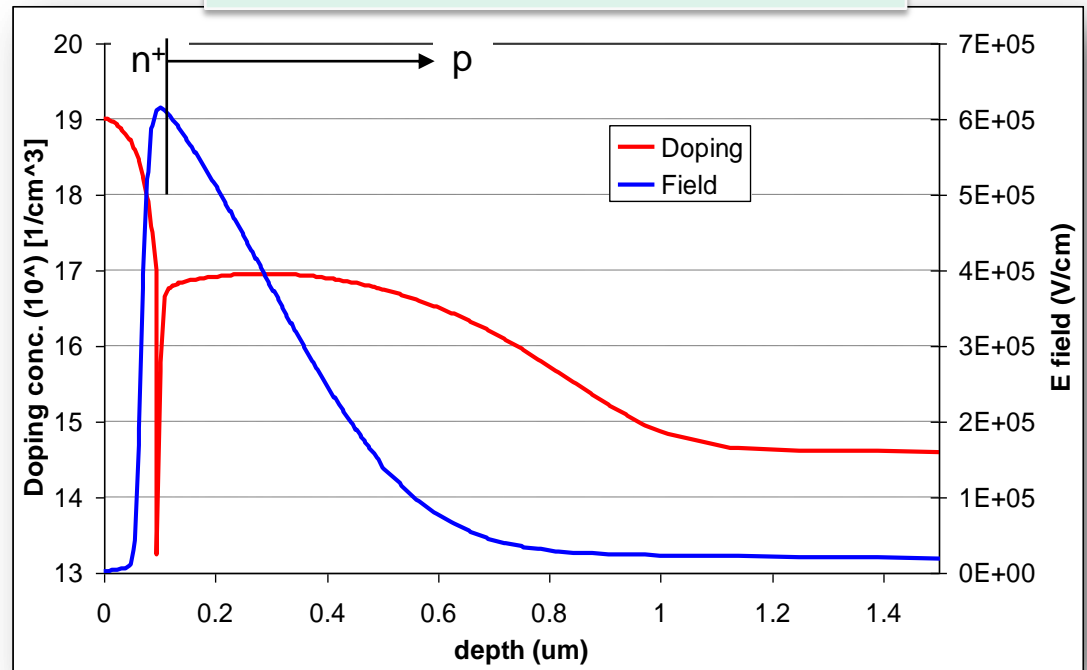
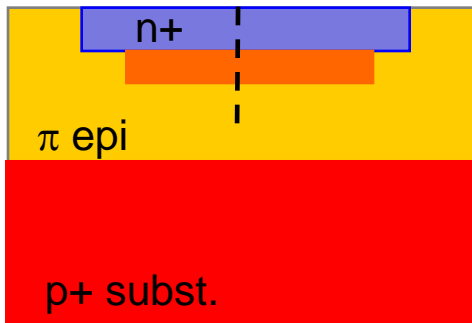
15-year experience in silicon radiation detectors

# SiPM Technology

Developed in 2005

## Shallow-Junction SiPM

Cross section



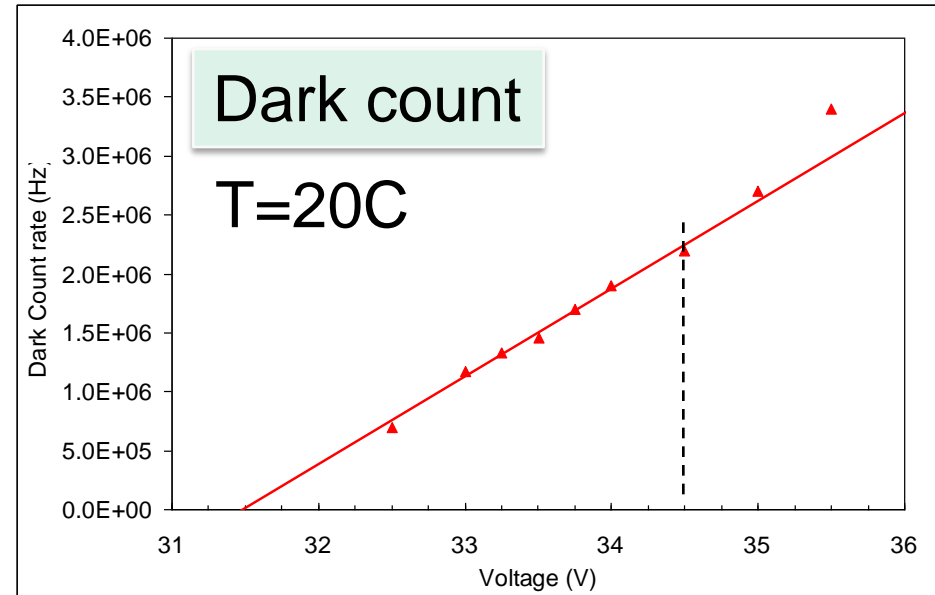
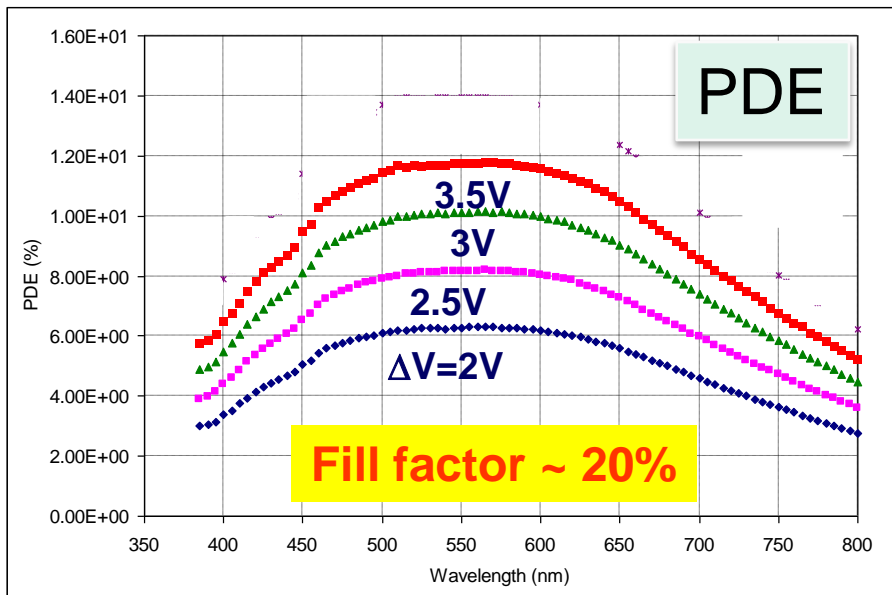
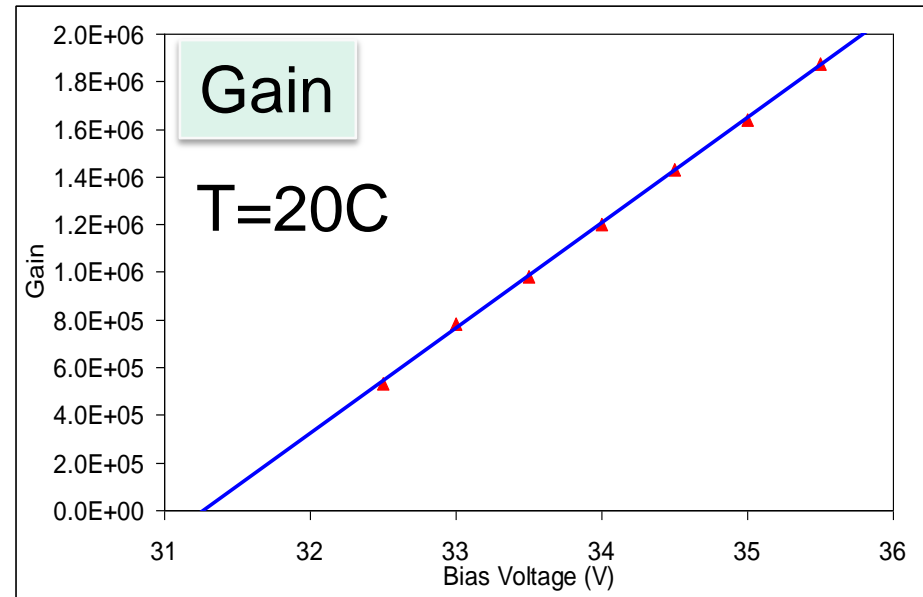
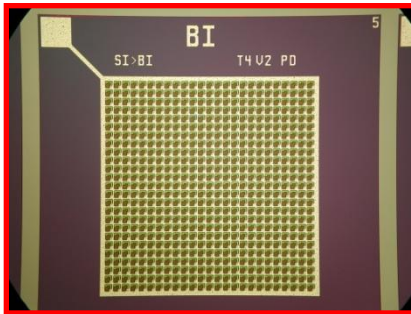
Standard approach but with two peculiarities:

- 1) Very shallow junction
- 2) ARC optimized for short wavelengths

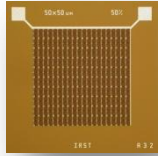
⇒ To enhance QE at short wavel.

# NSS 2006 – San Diego

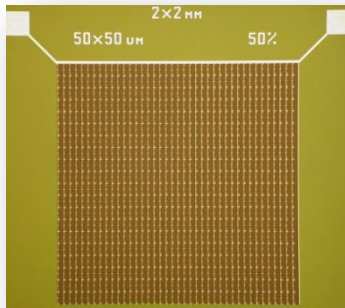
Only 1 geometry: 1x1mm<sup>2</sup> with  
40x40μm<sup>2</sup> cell  
max fill factor 30%



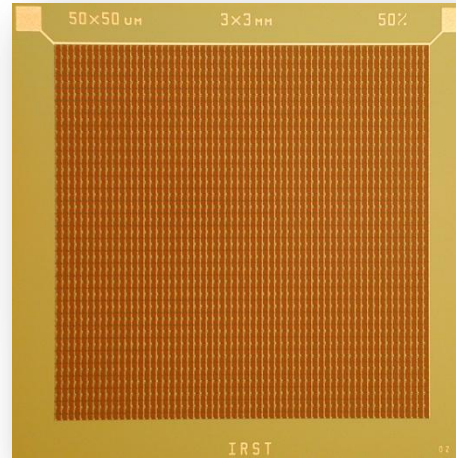
# NSS 2007 - Hawaii



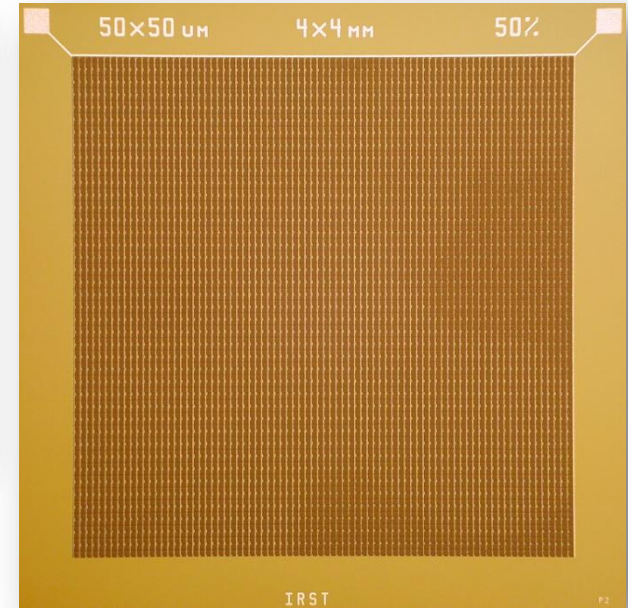
1x1mm<sup>2</sup>



2x2mm<sup>2</sup>



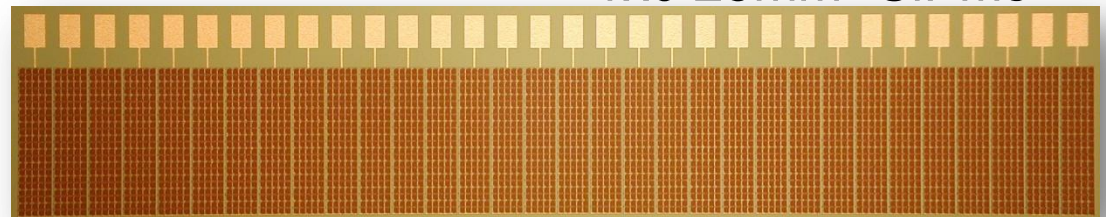
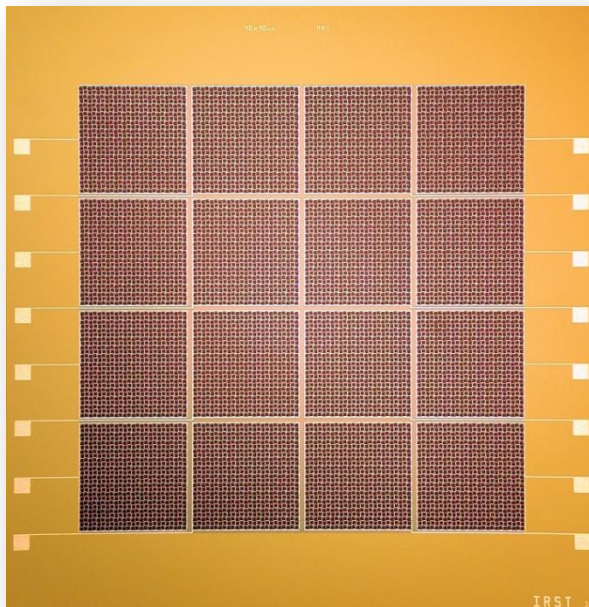
3x3mm<sup>2</sup> (3600 cells)



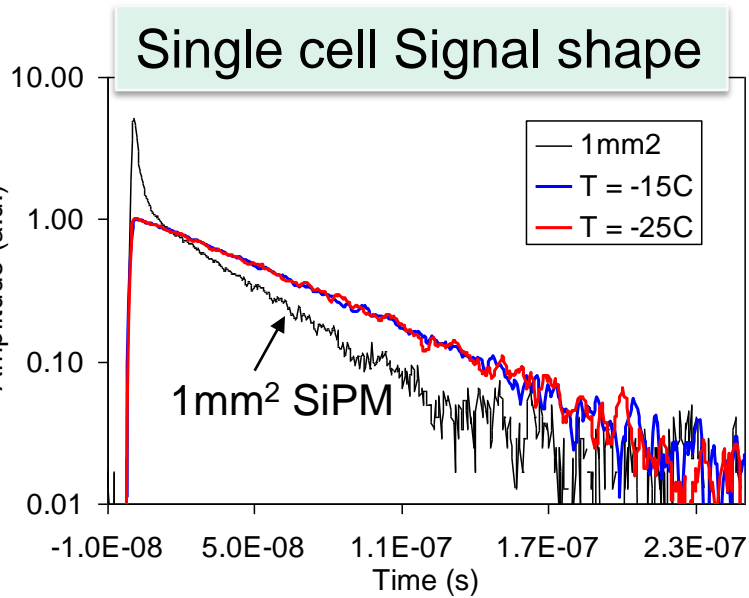
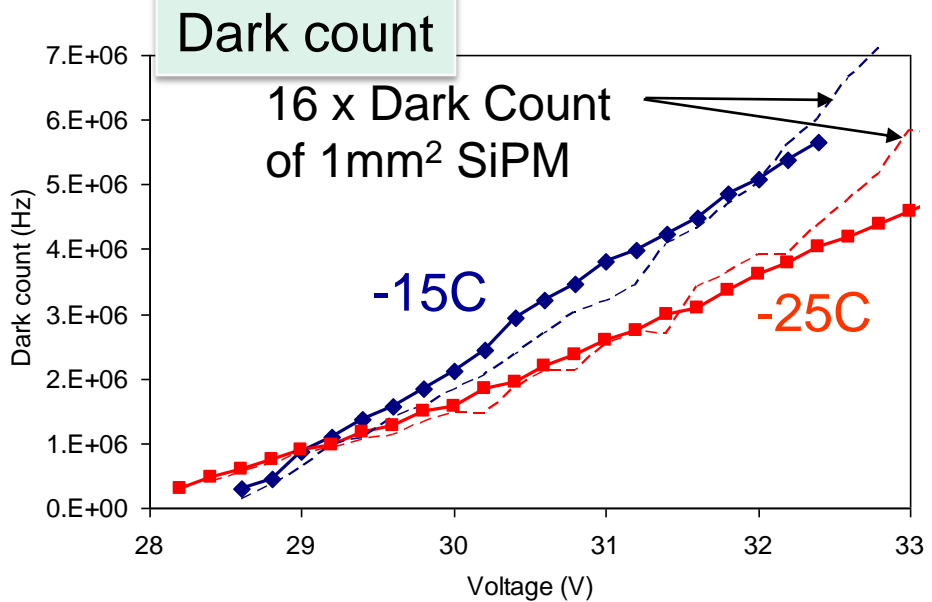
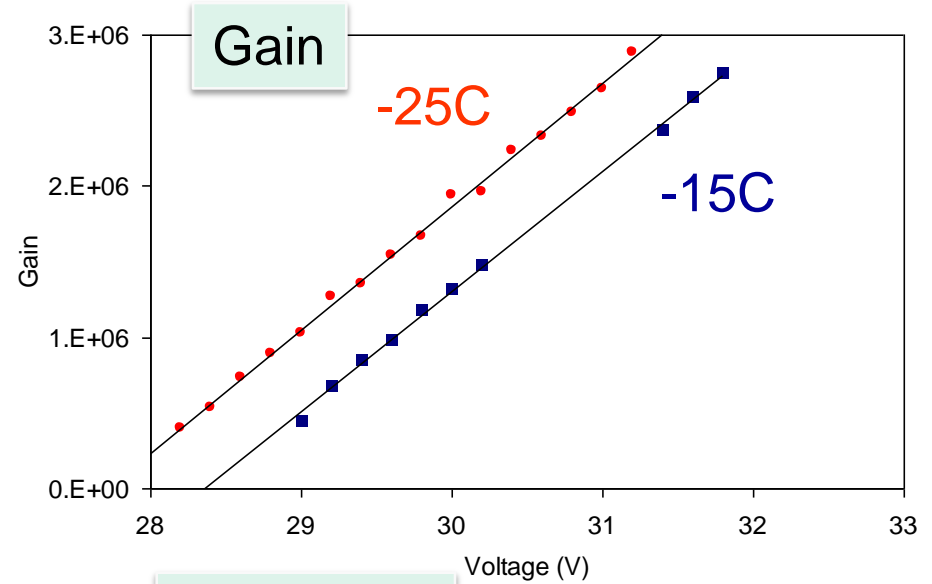
4x4mm<sup>2</sup> (6400 cells)

Matrices:  
4x4 elements  
of 1x1mm<sup>2</sup> SiPMs

Linear arrays:  
8,16,32 elements of  
1x0.25mm<sup>2</sup> SiPMs

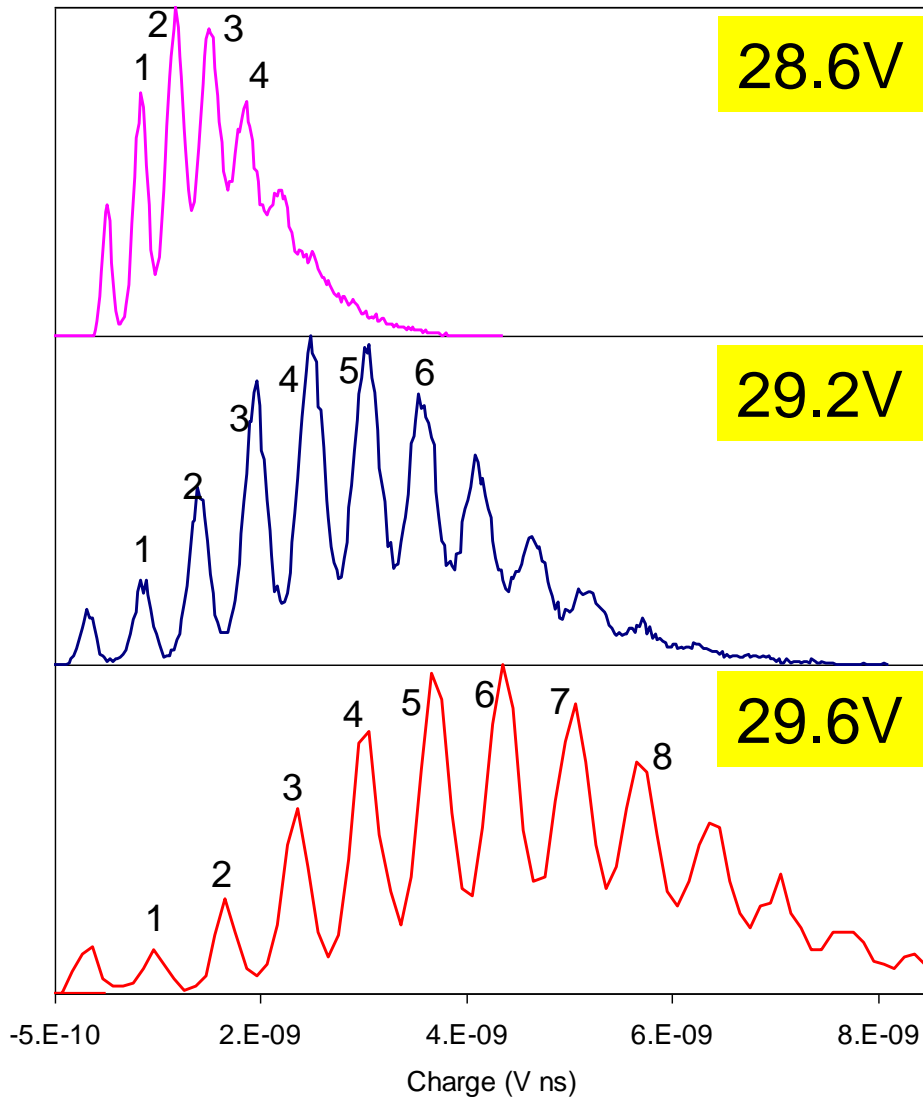


# 4x4mm<sup>2</sup> SiPM - 50x50mm<sup>2</sup> cell



# 4x4mm<sup>2</sup> SiPM - 50x50mm<sup>2</sup> cell

T=-25C V<sub>bd</sub>=27.6V



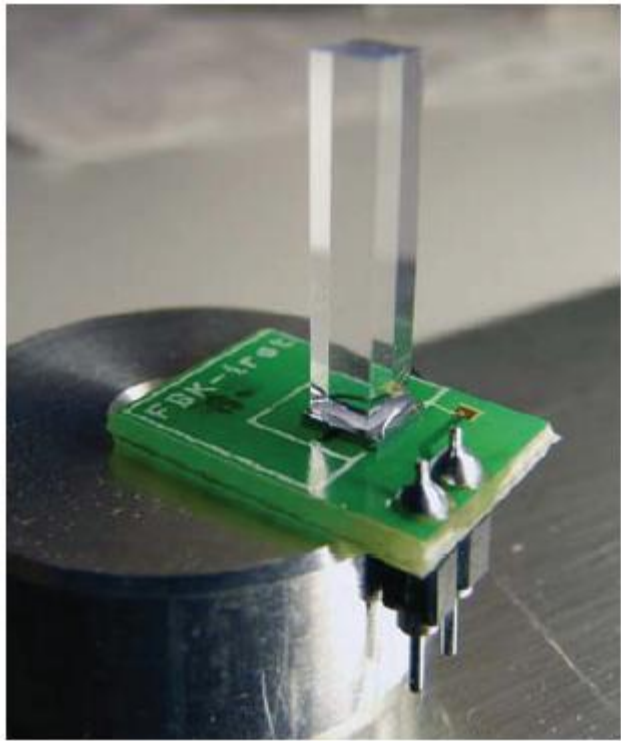
Charge spectra under illumination with short low-intensity light pulses

- Excellent cell response uniformity over the entire device (6400 cells)
- Width of peaks dominated by electronic noise



# 4x4mm<sup>2</sup> SiPM - 50x50mm<sup>2</sup> cell

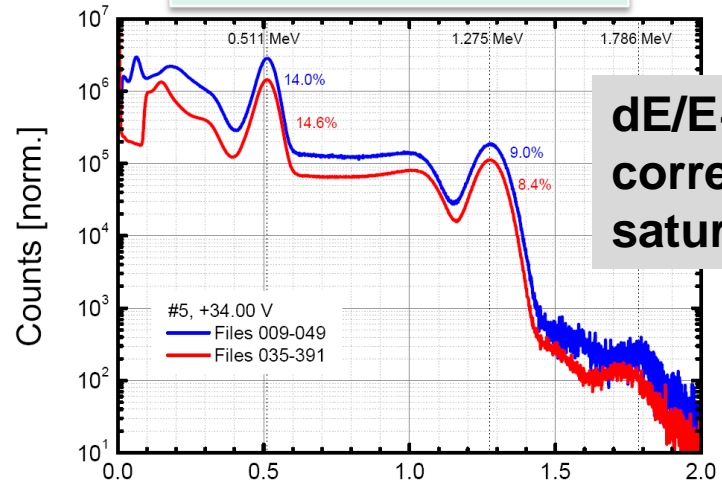
**PET application:  
SiPM + LYSO**



Measurements by Philips Aachen

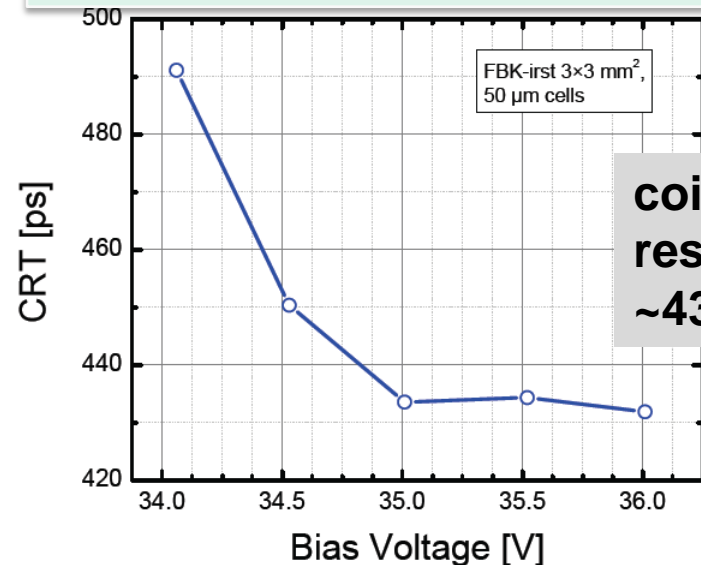
C. Piemonte

## Energy resolution



**dE/E ~ 14%  
corrected for  
saturation**

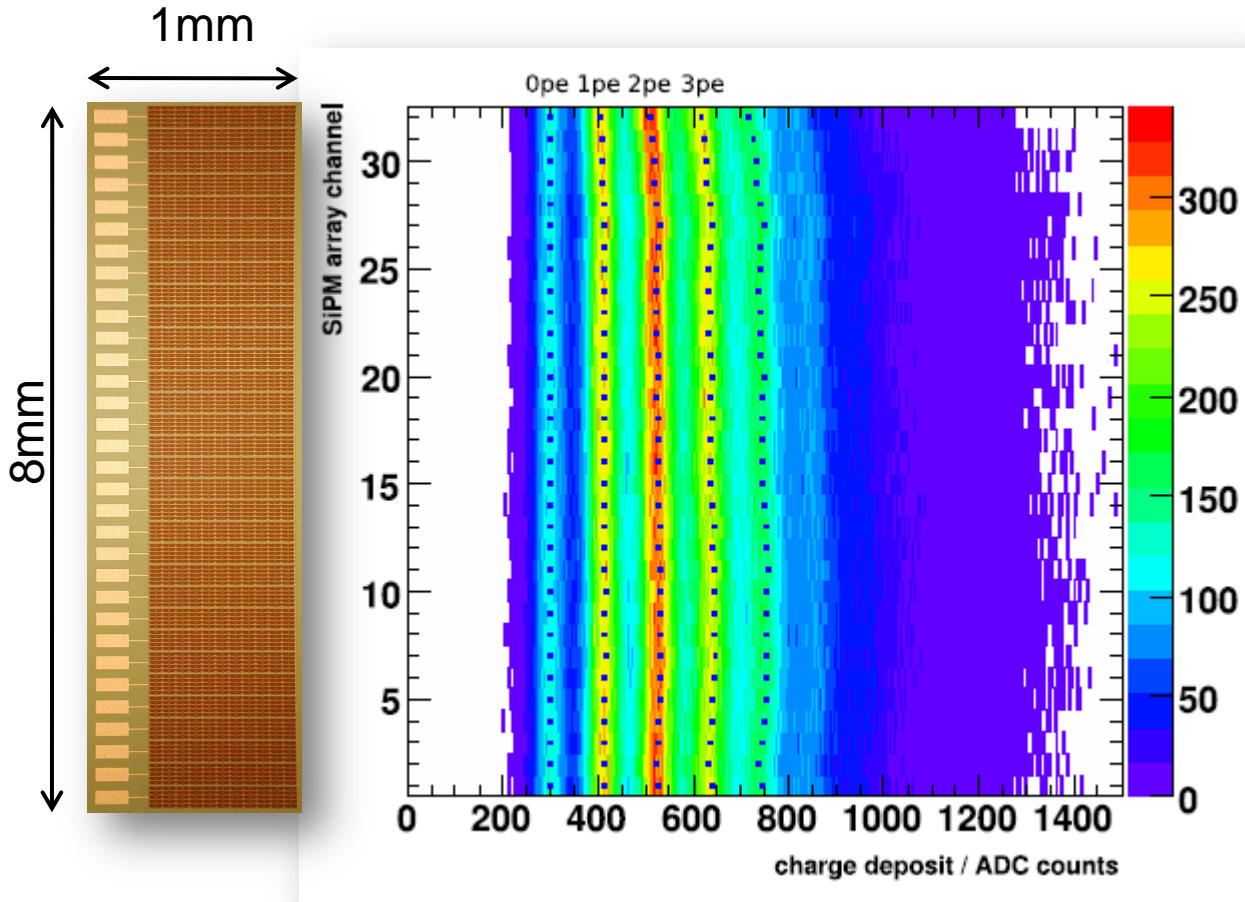
## Coincidence time resolution



**coincidence  
resolution  
~430ps**

# Response uniformity

## SiPM array for fiber tracking application



Charge deposited versus SiPM array channel under illumination with a pulsed LED.

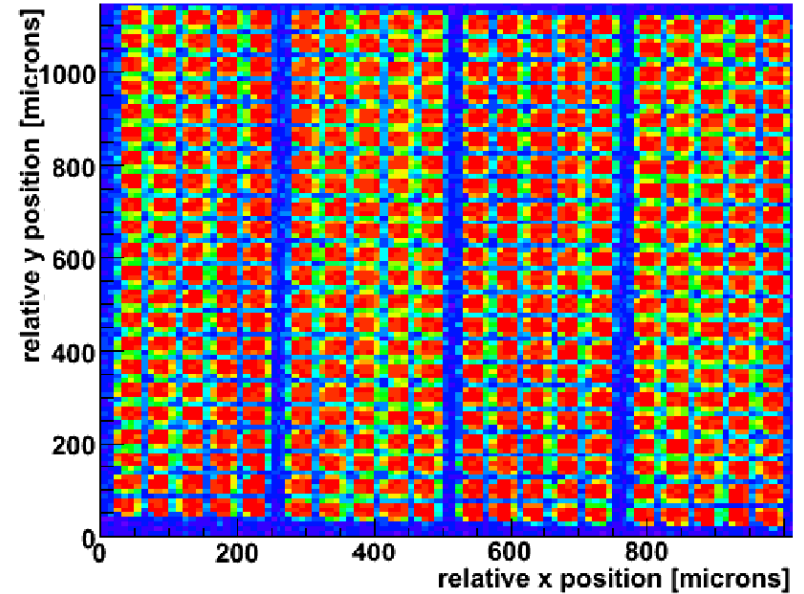
Gain variation of 2%

R. Greim, H. Gast, T. Kirn,  
J. Olzem, G. Roper Yearwood,  
S. Schael, N. Zimmermann,  
G. Ambrosi;c, R. Battiston;  
C. Piemonte  
presented at Siena conference  
2008

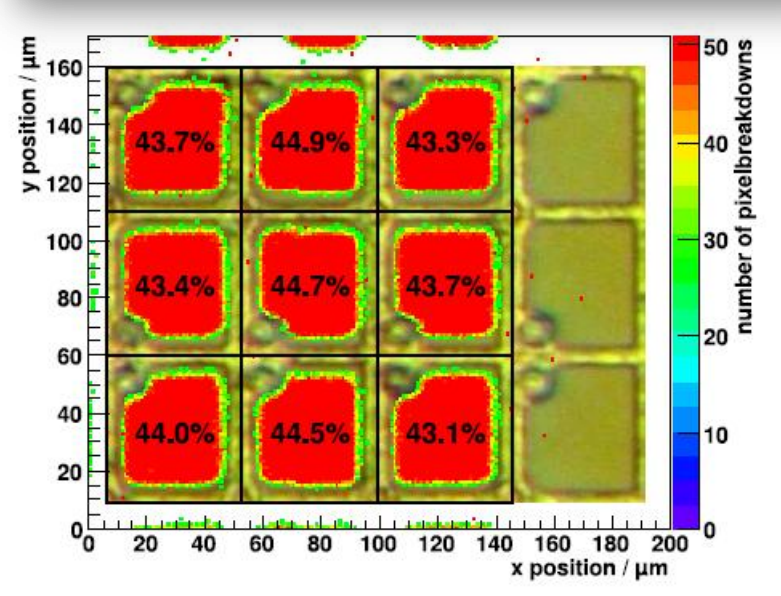
# Cell functionality and fill factor

Illumination with a LED  
spot diameter of  $\sim 5 \mu\text{m}$ .

Coarse step to verify  
functionality of cells



Fine step to estimate  
the fill factor



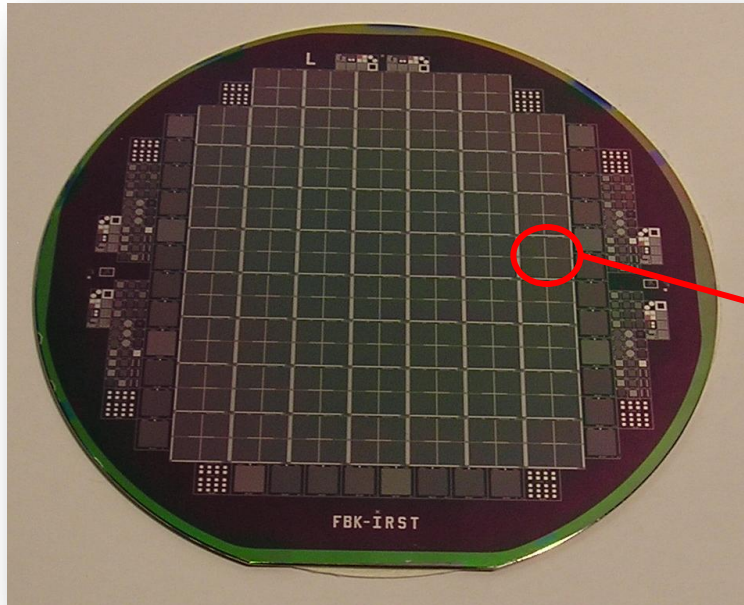
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presented at Siena conference  
2008

# 2008/09 – large area devices & first productions

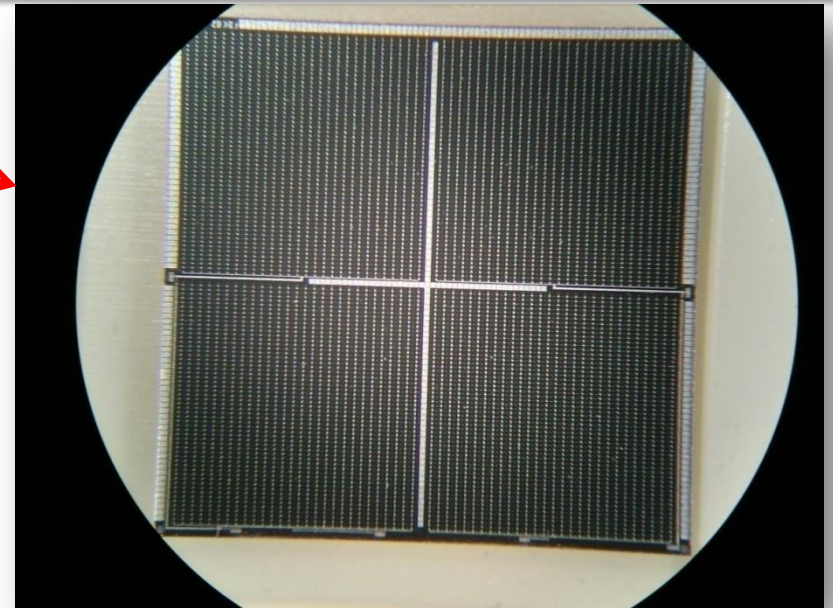
HyperImage EU-funded project ([www.hybrid-pet-mr.eu](http://www.hybrid-pet-mr.eu))

Finalized small production for first small animal PET/MR

Produced ~700 fully working arrays

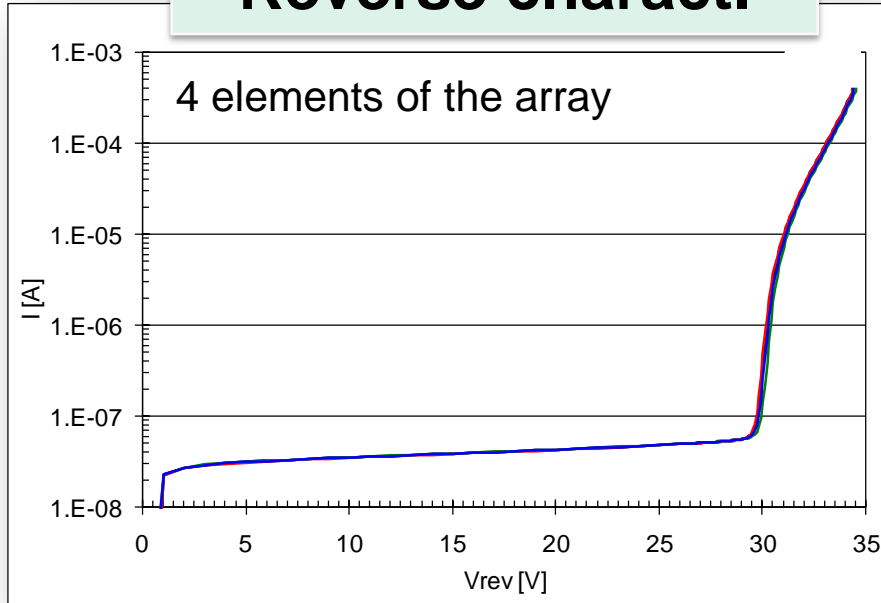


2x2 array of  $\sim 4 \times 4 \text{mm}^2$  SiPMs



# HI SiPM - testing procedure

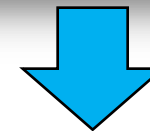
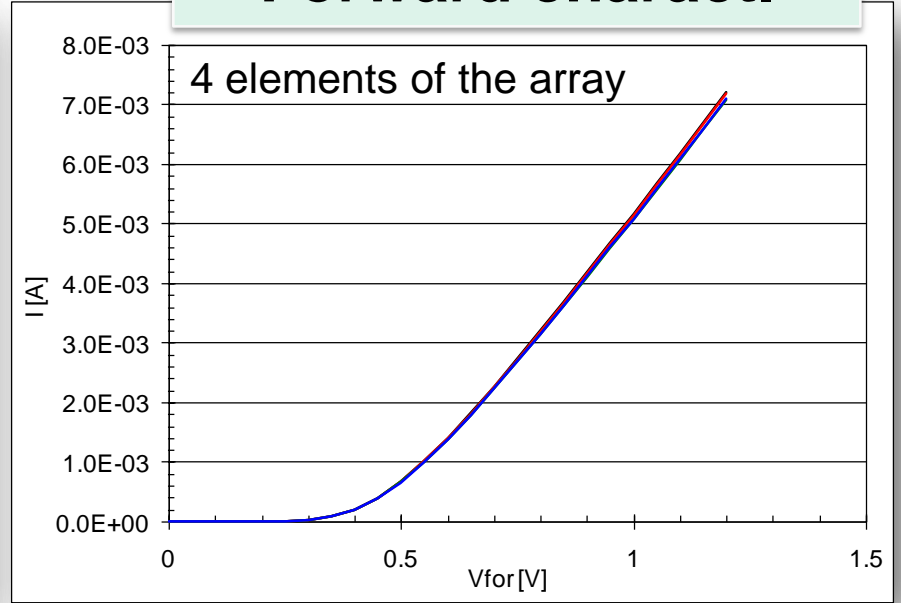
## Reverse charact.



Info we get

- Functionality of the device
- Breakdown voltage
- Dark count estimate

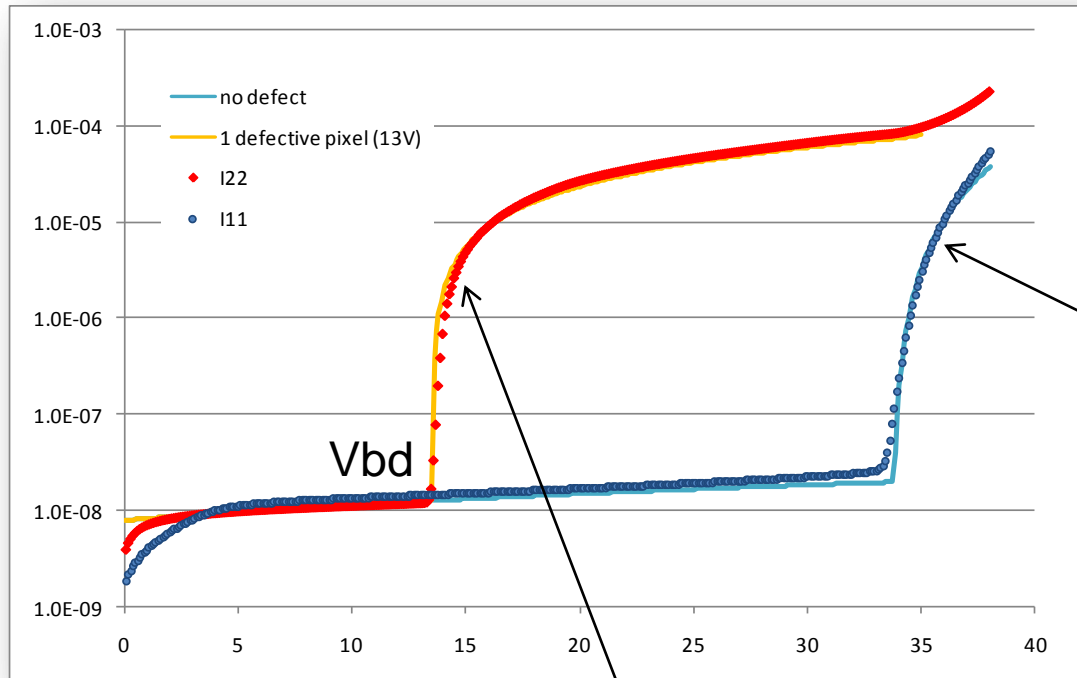
## Forward charact.



- Functionality of the device
- Resistor value estimate

# HI SiPM – faulty devices

Most common defect is premature breakdown

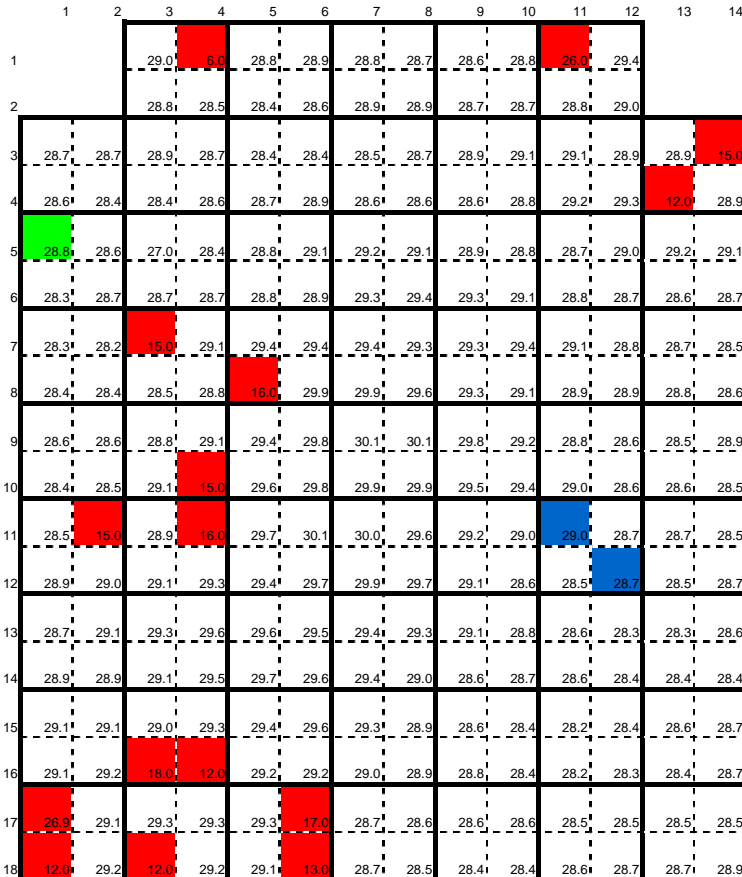


working SiPM.  
The current can  
be roughly modeled  
as  $I=q \cdot DC \cdot G$

SiPM with 1 defective cell.  
The current can be modeled  
as  $I=(V-V_{bd})/R_q$

# HI SiPM – summary of a wafer test (good one)

## Wafer map

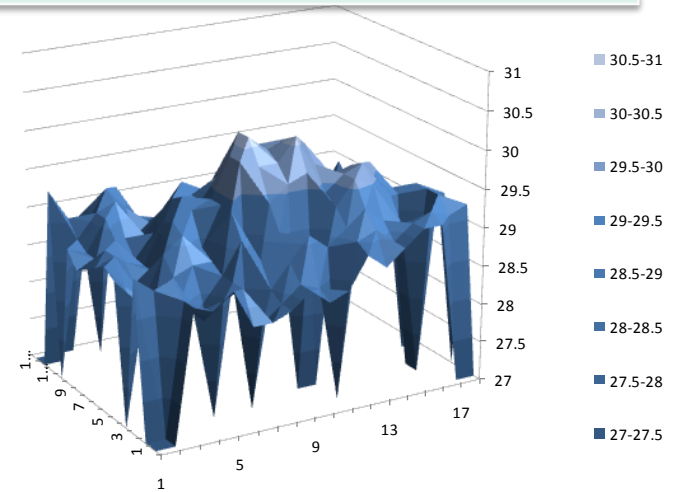


white = OK

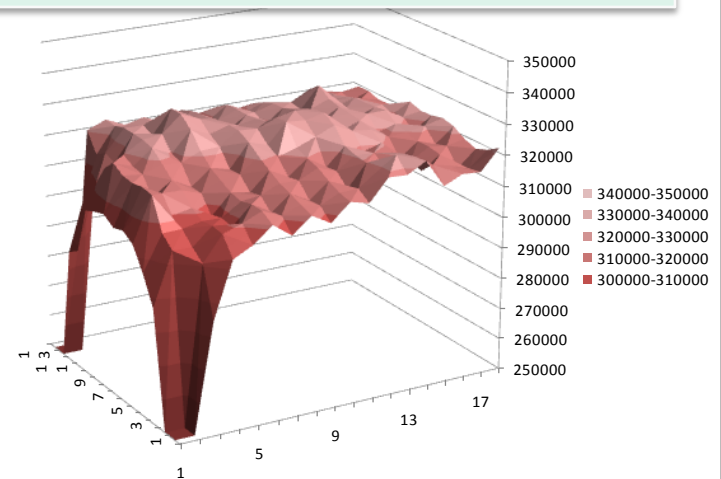
red = premature breakdown

green/blue = problems after breakdown

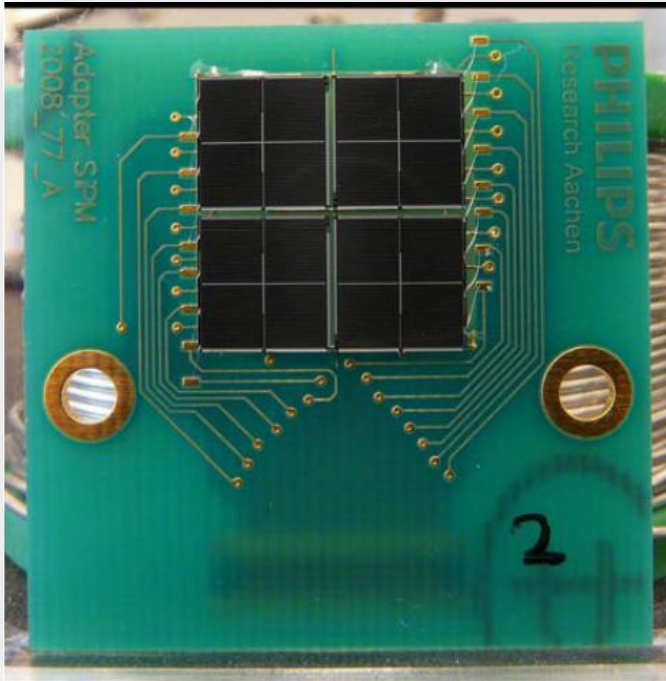
## Breakdown voltage



## Polysilicon resistor

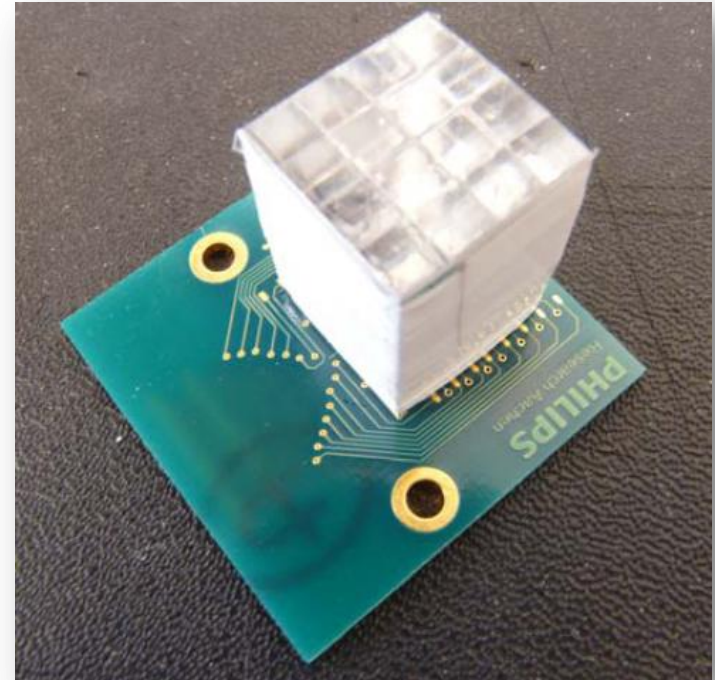


# HI SiPM – first functional tests ongoing



4 arrays mounted on  
test PCD

LYSO crystal mounted  
on the SiPMs

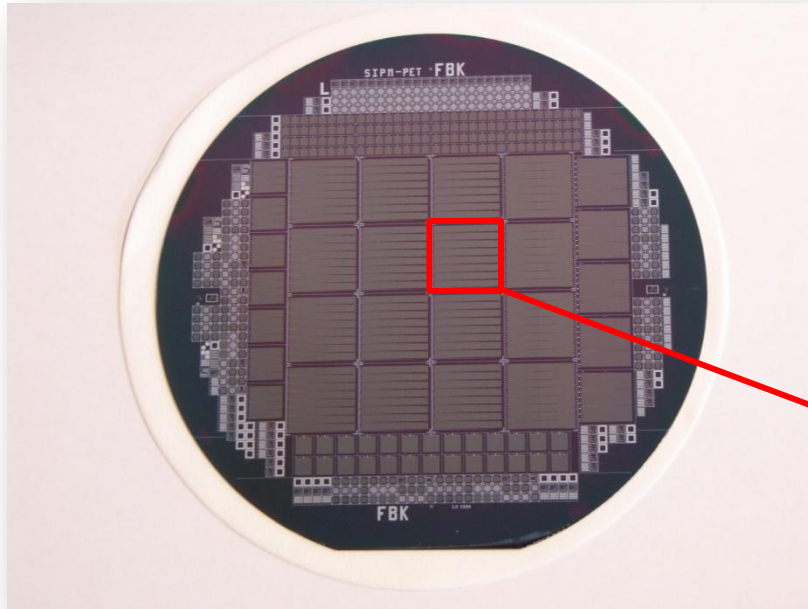


mounting @ Philips Aachen

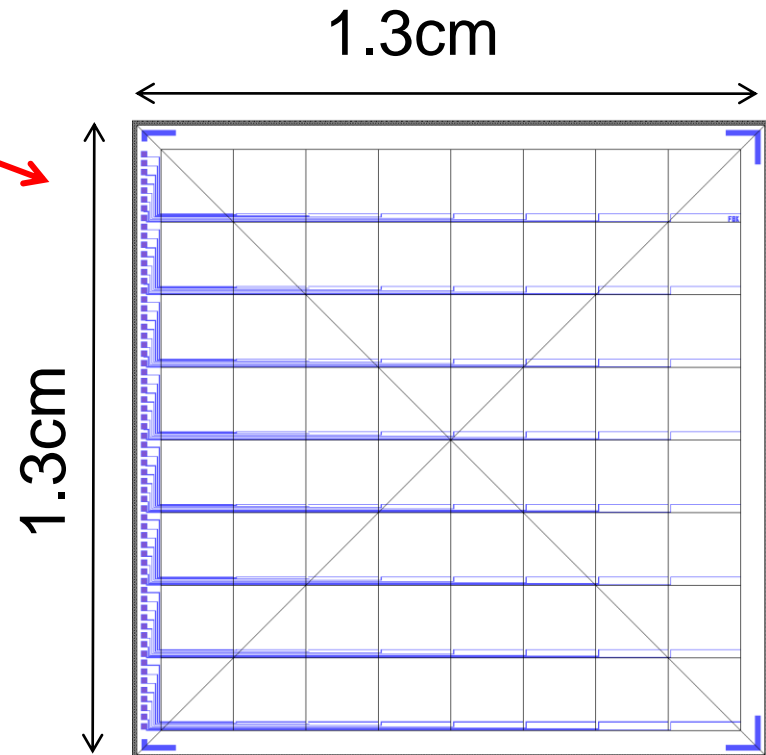


# Arrays for INFN-DaSiPM2 project

INFN Pisa  
Bari  
Bologna  
Perugia  
Trento



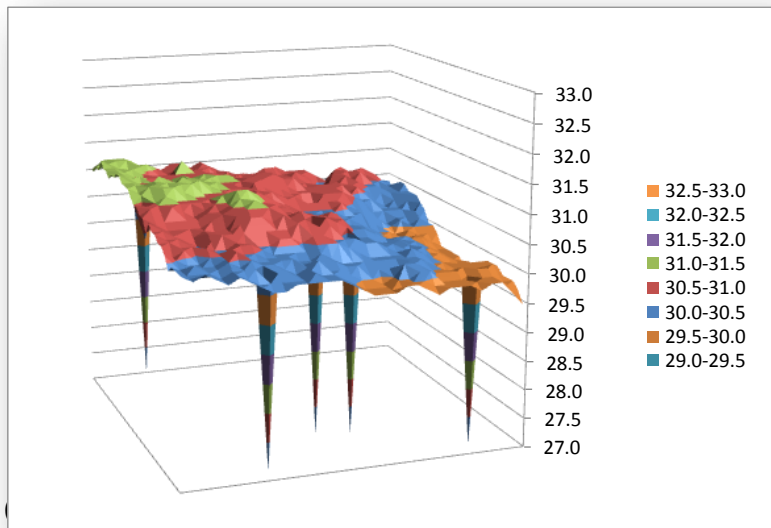
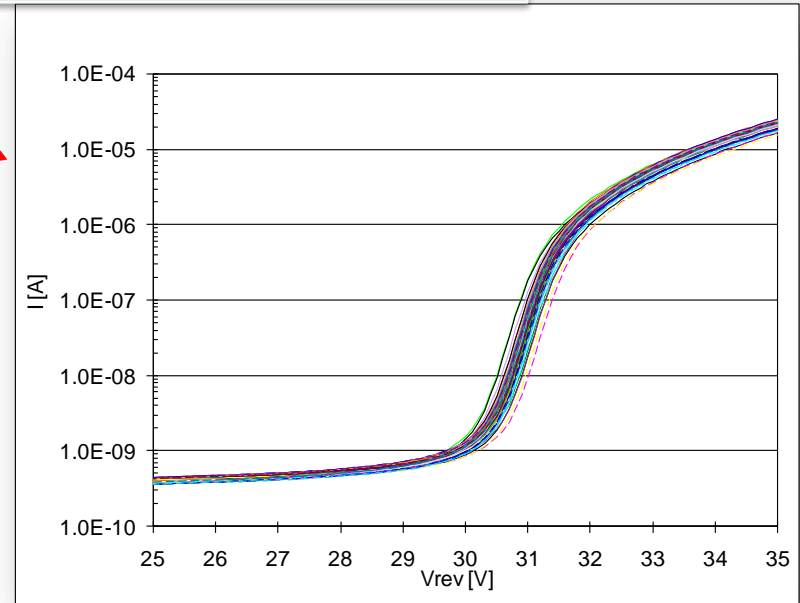
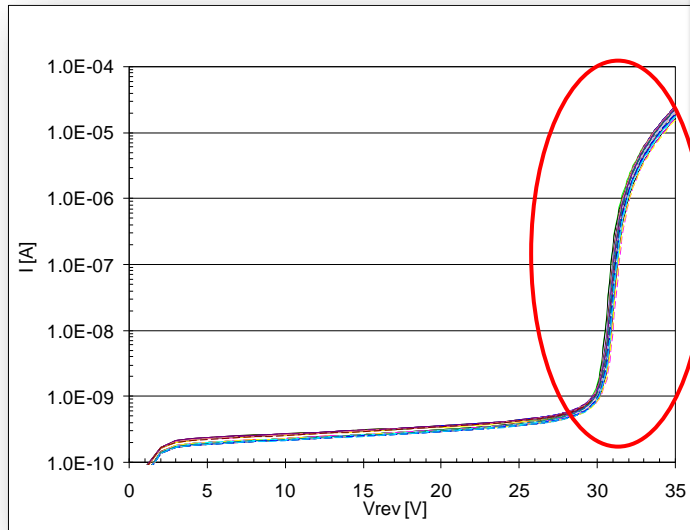
- 8x8 array
- 1.5mm element pitch
- read-out on one side



**So far, our largest area monolithic array!!**

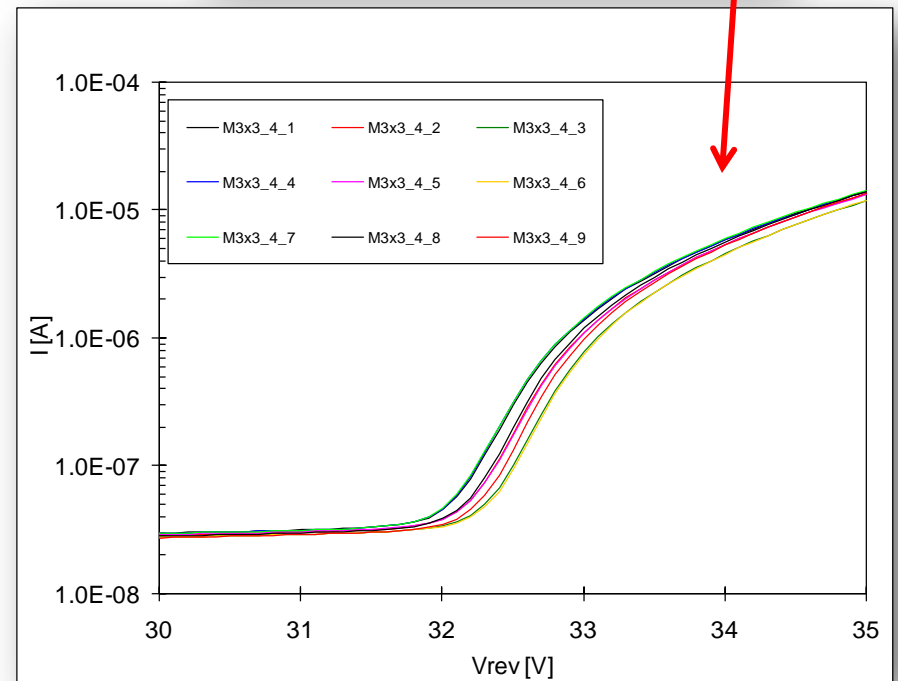
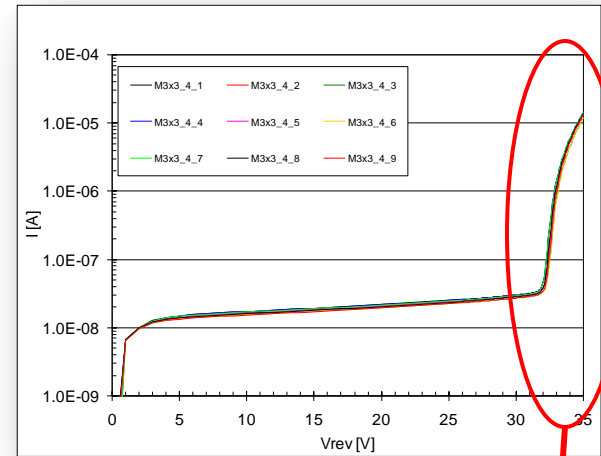
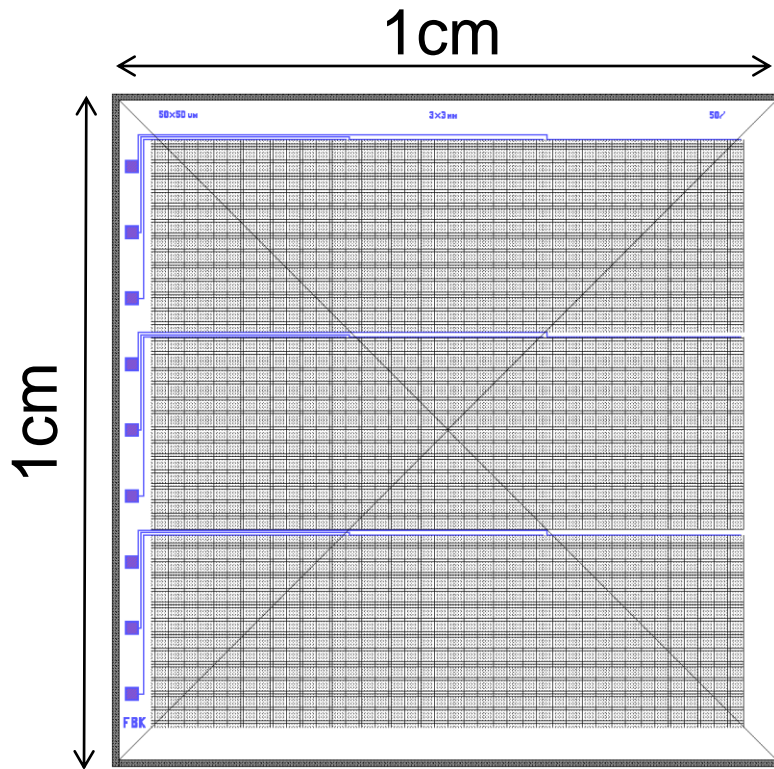
# DaSiPM2 Arrays, IV

IV plot of the 64 elements of the array



Breakdown voltage over the entire wafer surface

# 3x3 array of 3x3mm<sup>2</sup> SiPMS



# Conclusion

- **Collaborations both in nuclear medicine and HEP**
- **We are moving towards large area monolithic arrays.**
  - Long tedious work to understand origin of defects and improve yield
  - Working to improve BD uniformity
- **R&D:**
  - **on array/SiPM interconnectivity;**
  - **new SiPM technology.**